SK75GAR12T4



SEMITOP® 2

IGBT Module

SK75GAL12T4 SK75GAR12T4

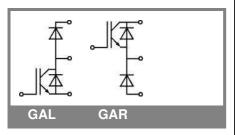
Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

Typical Applications*

Remarks

• V_{CE,sat} , V_F = chip level value



Ahsolui	te Maximum Ratings	T	s = 25 °C, unless otherwise s	pecified
Symbol			Values	Units
IGBT	Conditions		values	Units
V _{CES}	T _j = 25 °C		1200	V
I _C	T _i = 175 °C	T _s = 25 °C	80	Α
O	J	T _s = 70 °C	65	Α
I _{CRM}	I _{CRM} = 3 x I _{Cnom}		225	Α
V _{GES}			± 20	V
t _{psc}	V_{CC} = 800 V; $V_{GE} \le 15$ V; $V_{CES} < 1200$ V	T _j = 150 °C	10	μs
Inverse	Diode		·	
I _F	T _j = 175 °C	$T_s = 25 ^{\circ}C$	20	Α
		$T_s = 70 ^{\circ}C$	16	Α
I_{FRM}	I _{FRM} = 3 x I _{Fnom}		45	Α
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	90	Α
	eeling Diode		·	
I _F	T _j = 175 °C	$T_S = 25 ^{\circ}C$	70	Α
		$T_S = 70 ^{\circ}C$	55	Α
I _{FRM}	I _{FRM} = 3xI _{Fnom}		225	Α
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	425	Α
Module			·	
$I_{t(RMS)}$				Α
T _{vj}			-40 + 175	°C
T _{stg}			-40 +125	°C
V _{isol}	AC, 1 min.		2500	V

Characteristics		T _s =	T _s = 25 °C, unless otherwise specified					
Symbol	Conditions		min.	typ.	max.	Units		
IGBT								
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5	5,8	6,5	V		
I _{CES}	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T _j = 25 °C			1,0	mA		
		$T_j = 150 ^{\circ}\text{C}$ $T_i = 25 ^{\circ}\text{C}$				mA		
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			600	nA		
		$T_j = 150 ^{\circ}\text{C}$ $T_i = 25 ^{\circ}\text{C}$				nA		
V _{CE0}				1,1	1,3	V		
		T _j = 150 °C		1	1,2	V		
r _{CE}	V _{GE} = 15 V	T _j = 25°C		10		mΩ		
		$T_{j} = 150^{\circ}C$		16		mΩ		
V _{CE(sat)}	I _{Cnom} = 75 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,85	2,05	V		
		$T_j = 150^{\circ}C_{chiplev.}$		2,25	2,45	V		
C _{ies}				4,4		nF		
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,29		nF		
C _{res}				0,235		nF		
Q_G	V _{GE} =-7V+15V			570		nC		
R _{Gint}	T _j = 25 °C			10		Ω		
t _{d(on)}				50		ns		
t _r	R_{Gon} = 15 Ω	$V_{CC} = 600V$		60		ns		
E _{on}	di/dt = 2000 A/μs	I _C = 75A		13		mJ		
t _{d(off)}	$R_{Goff} = 15 \Omega$	T _j = 150 °C		500		ns		
t _f		V _{GE} = -7/+15V		60		ns		
E _{off}				7		mJ		
$R_{th(j-s)}$	per IGBT			0,74		K/W		

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Features

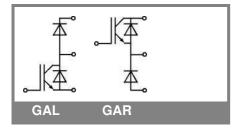
- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

Typical Applications*

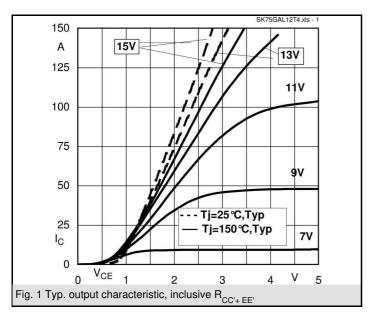
Remarks

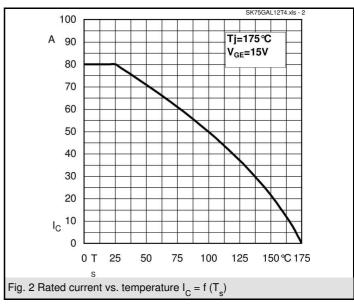
• V_{CE,sat} , V_F = chip level value

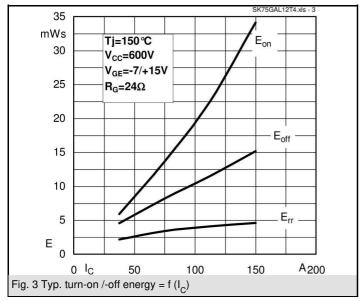
Characteristics									
Symbol	Conditions	İ	min.	typ.	max.	Units			
Inverse Diode									
$V_F = V_{EC}$	$I_{Fnom} = 15 \text{ A}; V_{GE} = 0 \text{ V}$			2,38	2,71	V			
		$T_j = 150 ^{\circ}\text{C}_{\text{chiplev.}}$ $T_j = 25 ^{\circ}\text{C}$		2,44	2,77	V			
V_{F0}				1,3	1,5	V			
		T _j = 150 °C		0,9	1,1	V			
r _F		T _j = 25 °C		72	80,7	mΩ			
		T _j = 150 °C		102,8	111,6	mΩ			
I _{RRM}	I _F = A	T _j = 150 °C				A			
Q _{rr}	.,					μC			
E _{rr}	V _{CC} = 600V					mJ			
$R_{th(j-s)D}$	per diode			2,34		K/W			
	eling Diode								
$V_F = V_{EC}$	I_{Fnom} = 75 A; V_{GE} = 0 V	$T_j = 25 ^{\circ}C_{\text{chiplev.}}$		2,1	2,5	V			
		$T_j = 150 ^{\circ}C_{\text{chiplev.}}$		2,4	2,5	V			
V_{F0}		T _j = 25 °C		1,3	1,5	V			
		T _j = 150 °C		0,9	1,1	V			
r _F		T _j = 25 °C		12	13,3	V			
		T _j = 150 °C		16	17,3	V			
I _{RRM}	I _F = 75 A	T _j = 150 °C		45		Α			
Q _{rr}	di/dt = 2000 A/μs			10		μC			
E _{rr}	V _{CC} = 600V			3		mJ			
$R_{th(j-s)FD}$	per diode			0,97		K/W			
M_s	to heat sink				2,5	Nm			
w				30		g			
Temperat	ure sensor								
R ₁₀₀	T_s =100°C (R_{25} =5k Ω)			493±5%		Ω			

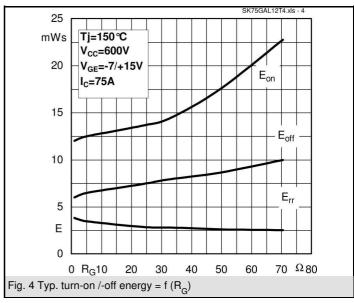


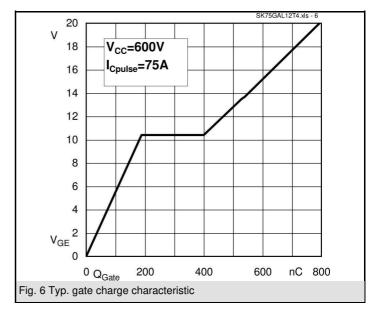
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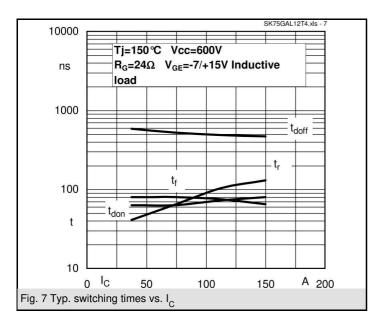


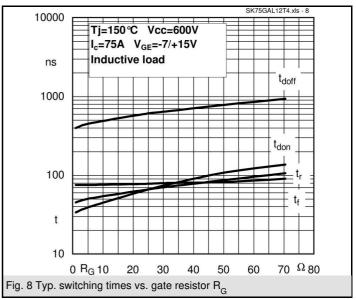


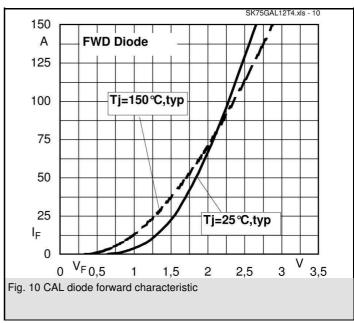


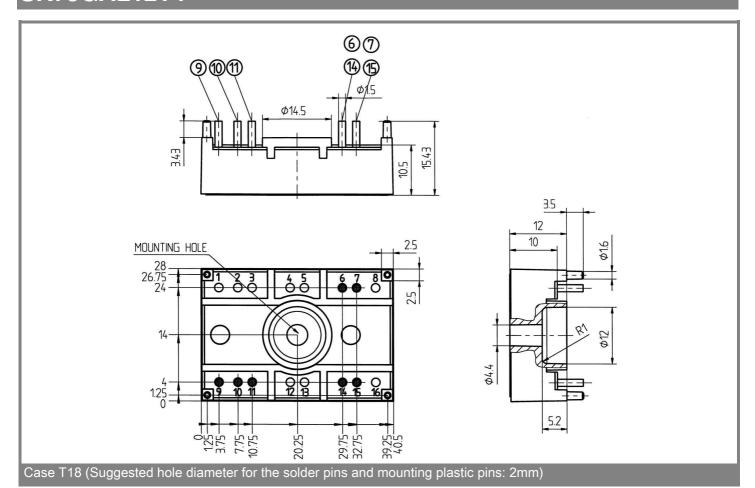


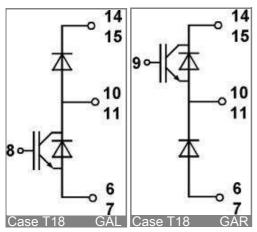
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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